

L Number	Hits	Search Text	DB	Time stamp
1	1874	simulat\$3 same wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:32
2	2	(simulat\$3 same wafer ) same (tungsten near silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:27
3	92	(simulat\$3 same wafer ) same (test near wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:27
4	5	(simulat\$3 same wafer ) same ((test near wafer) same (standard near2 wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:32
5	56	((test near wafer) same (standard near2 wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:33
6	256260	(photoresist or polymer or resin) same (silicon or tantalum or nickel or aluminum or tungsten)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:36
7	6434	((photoresist or polymer or resin) same (silicon or tantalum or nickel or aluminum or tungsten)) same bak\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:37
9	12	(((((photoresist or polymer or resin) same (silicon or tantalum or nickel or aluminum or tungsten)) same bak\$3) same simulat\$3) same simulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:43
10	7	(((((photoresist or polymer or resin) same (silicon or tantalum or nickel or aluminum or tungsten)) same bak\$3) same simulat\$3) same simulat\$3) and @pd<19990331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:43
8	12	(((((photoresist or polymer or resin) same (silicon or tantalum or nickel or aluminum or tungsten)) same bak\$3) same simulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:13
11	1838	(coat\$3 or deposit\$3) same ((mixture or combination) same (silicon and photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:23
12	5	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon and photoresist))) and (simulat\$3 same wafer )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:17
13	340	(coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:27

14	1	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same simulat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:29
15	0	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same alouminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:30
16	54	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same aluminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:33
17	29	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same aluminum)) and @pd<19990331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:34
18	181	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and @pd<19990331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:30
19	1	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and @pd<19990331) and (simulat\$3 same wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:29
20	0	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and @pd<19990331) and 428/698-702.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:30
21	27856	(simulat\$3 or calibrat\$3 or test\$3) same wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:36
22	40	((simulat\$3 or calibrat\$3 or test\$3) same wafer ) and ((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 18:36
-	1863	simulat\$3 same wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 16:11
-	24	(simulat\$3 same wafer) same (photoresist same silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 20:54
-	12	((simulat\$3 same wafer) same (photoresist same silicon)) and @pd<19990331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 20:56
-	0	(simulat\$3 same wafer).clms.	USPAT; US-PGPUB	2003/06/26 20:38
-	105	(simulat\$3 same wafer).clm.	USPAT; US-PGPUB	2003/06/26 20:39
-	32	((simulat\$3 same wafer).clm.) and @pd<19990331	USPAT; US-PGPUB	2003/06/26 20:40